ON Semiconductor

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RHRP3060 30 A, 600 V Hyperfast Diodes

Features

- Hyperfast Recovery trr = 45 ns (@ IF = 30 A)
- Max Forward Voltage, V_F = 2.1 V (@ T_C = 25°C)
- · 600 V Reverse Voltage and High Reliability
- · Avalanche Energy Rated
- · RoHS Compliant

Applications

- · Switching Power Supplies
- · Power Switching Circuits
- General Purpose

Ordering Informations

Part Number	Packaç		E 'nd
RHRP3060	TO-220AC	L	HRF 3060

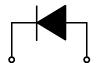
Description

The RHRP3060 is a hyperfast diodr and it recovery characteristics. It has the half recovery time if ultrafast diodes and is silicon nitride assiva. It ioning lanted epitaxial planar construction. The educate intercled to be used as freewhering coupling diodes and diodes in a variety of switching powers in a planar construction. For all grand other power switching populations, and other power switching oping tions. For all grand electrical noise in recovery switching grand constructions and electrical noise in recovery switching grand constructions.

Pin Assig ments



TO-220



1. Cathode 2. Anode

Absolute Maximum Ratings

Symbol	Parameter	RHRP3060	Unit
V _{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 120°C)	30	A
I _{FRM}	Repetitive Peak Surge Current (Square Wave, 20KHz)	70	A
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave, 1 Phase, 60Hz)	325	А
P _D	Maximum Power Dissipation	125	W
E _{AVL}	Avalanche Energy (See Figures 10 and 11)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature	-65 to 175	°C

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Test Conditions		RHRP3060		Unit
	rest conditions	Min.	Тур.	Max.	Jill
V _F	I _F = 30 A	-	-	2.1	V
	I _F = 30 A, T _C = 150°C	-	-	1.7	V
I _R	V _R = 400 V	-	-	-	μΑ
	V _R = 600 V	-	-	250	μΑ
	V _R = 400 V, T _C = 150°C	-	-	-	mA
	V _R = 600 V, T _C = 150°C	-	-	1.0	mA
t _{rr}	I _F = 1 A, dI _F /dt = 200 A/μs	-	-	40	ns
	I _F = 30 A, dI _F /dt = 200 A/μs	-	-	45	ns
t _a	I _F = 30 A, dI _F /dt = 200 A/μs	-	22	-	ns
t _b	I _F = 30 A, dI _F /dt = 200 A/μs	-	18		ns
Q_{RR}	I _F = 30 A, dI _F /dt = 200 A/μs	-	100		TC.
CJ	V _R = 600 V, I _F = 0 A	-	5		pF
$R_{\theta JC}$		-		1.2	°C/W
I_R = Instantaneo t_{rr} = Reverse red t_a = Time to read t_b = Time from p Ω_{RR} = Reverse red C_J = Junction C_a	apacitance. sistance junction to case.	ME	100	Fig (re 3).	TIOR
$\begin{split} & I_R = \text{Instantaneo} \\ & t_{rr} = \text{Reverse rec} \\ & t_a = \text{Time to reac} \\ & t_b = \text{Time from p} \\ & \Omega_{RR} = \text{Reverse rec} \\ & C_J = \text{Junction Ca} \\ & R_{eJC} = \text{Thermal res} \\ & pw = \text{pulse width} \end{split}$	us reverse current. covery time (See Figure 9), summation of t _a + t _b . ch peak reverse current (See Figure 9). eak I _{RM} to projected zero crossing of I _{RM} based on a stracovery charge. expacitance. sistance junction to case.	ME	100	Fig (re 9):	

Typical Performance Characteristics

Figure 1. Forward Current vs Forward Voltage

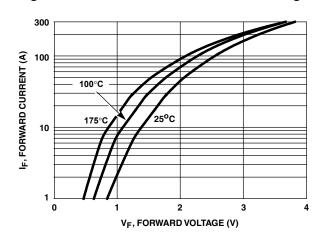


Figure 2. Reverse Currnt vs Reverse Voltage

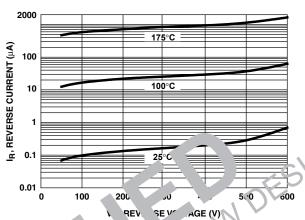
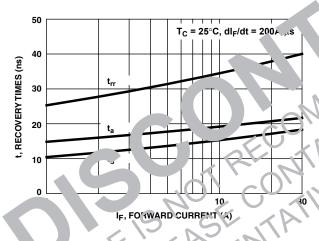


Figure 3. t_{rr}, t_a and t_b Curves vs Forward Current



F. ure t_{rr a} and t_b Curves vs

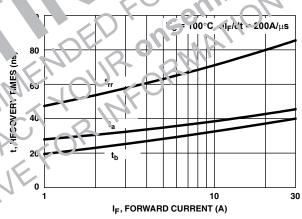


Figure 5. t_{rr}, t_a and t_b Curves vs Forward Current

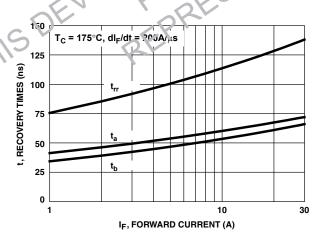
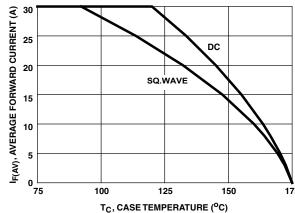
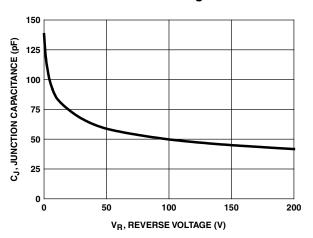


Figure 6. Current Derating Curve



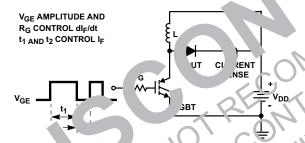
Typical Performance Characteristics (Continued)

Figure 7. Junction Capacitance vs Reverse Voltage

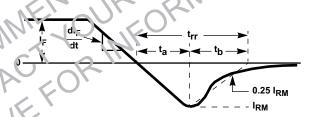


Test Circuit and Waveforms

Figure 8. t_{rr} Test Circuit



gure 9. t_{rr} Waveforms and Definitions



Figu + 10. Avalancine Energy Test Circuit

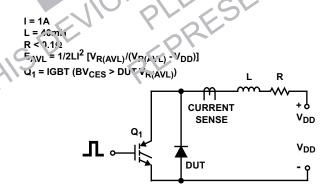
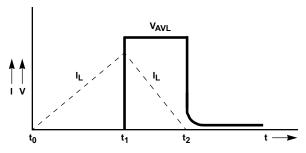


Figure 11. Avalanche Current and Voltage Waveforms





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